Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope V_{DS} = 480 V, I_D = 3.2 A, T_j = 125 °C	dv/dt	50	V/ns

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	3.3	K/W
Thermal resistance, junction - case, FullPAK	R_{thJC_FP}	-	-	4.1	
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
Thermal resistance, junction - ambient, FullPAK	R_{thJA_FP}	-	-	80	
SMD version, device on PCB: @ min. footprint @ 6 cm^2 cooling area [3)]	R_{thJA}	 - -	 - 35	 62 -	
Soldering temperature, wavesoldering 1.6 mm (0.063 in.) from case for 10s [4)]	T_{sold}	-	-	260	°C

Electrical Characteristics, at T_j=25°C unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=0.25mA	600	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	V_{GS}=0V, I_D=3.2A	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	I_D=135µA, V_{GS}=V_{DS}	2.1	3	3.9	
Zero gate voltage drain current	I_{DSS}	V_{DS}=600V, V_{GS}=0V, T_j=25°C T_j=150°C	 - -	 0.5 -	 1 70	µA
Gate-source leakage current	I_{GSS}	V_{GS}=30V, V_{DS}=0V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=2A T_j=25°C T_j=150°C	 - -	 1.26 3.8	 1.4 -	Ω
Gate input resistance	R_G	f=1MHz, open drain	-	10	-	

Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	g_{fs}	$V_{DS}\geq 2*I_D*R_{DS(on)max}$, I_D=2A	-	3.4	-	S
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, f=1MHz	-	400	-	pF
Output capacitance	C_{oss}		-	150	-	
Reverse transfer capacitance	C_{rss}		-	5	-	
Effective output capacitance,[5] energy related	$C_{o(er)}$	V_{GS}=0V, V_{DS}=0V to 480V	-	12	-	
Effective output capacitance,[6] time related	$C_{o(tr)}$		-	26	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=350V, V_{GS}=0/10V, I_D=3.2A, R_G=20Ω	-	7	-	ns
Rise time	t_r		-	3	-	
Turn-off delay time	$t_{d(off)}$		-	64	100	
Fall time	t_f		-	12	20	

Gate Charge Characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Gate to source charge	Q_{gs}	V_{DD}=420V, I_D=3.2A	-	2	-	nC
Gate to drain charge	Q_{gd}		-	6	-	
Gate charge total	Q_g	V_{DD}=420V, I_D=3.2A, V_{GS}=0 to 10V	-	13	17	
Gate plateau voltage	$V_{(plateau)}$	V_{DD}=420V, I_D=3.2A	-	5.5	-	V

[0]J-STD20 and JESD22

[1]Limited only by maximum temperature

[2]Repetitve avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR}*f$.

[3]Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical without blown air.

[4]Soldering temperature for TO-263: 220°C, reflow

[5]$C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

[6]$C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

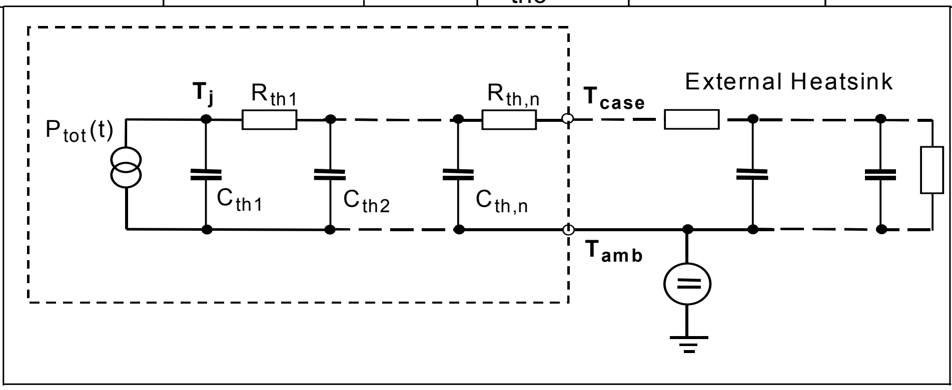
[7]I_{SD}<=I_D, di/dt<=400A/us, V_{DClink}=400V, V_{peak}<$V_{BR, DSS}$, T_j<$T_{j,max}$.
Identical low-side and high-side switch.

Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	T_C=25°C	-	-	3.2	A
Inverse diode direct current, pulsed	I_{SM}		-	-	9.6	
Inverse diode forward voltage	V_{SD}	V_{GS}=0V, I_F=I_S	-	1	1.2	V
Reverse recovery time	t_{rr}	V_R=420V, I_F=I_S , di_F/dt=100A/µs	-	250	400	ns
Reverse recovery charge	Q_{rr}		-	1.8	-	µC
Peak reverse recovery current	I_{rrm}		-	15	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt	T_j=25°C	-	-	-	A/µs

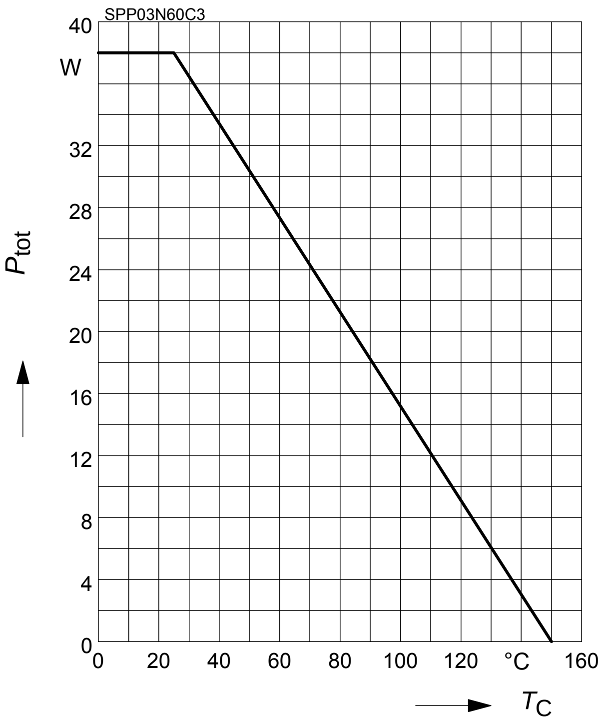
Typical Transient Thermal Characteristics

Symbol	Value		Unit	Symbol	Value		Unit
	SPP	SPA			SPP	SPA	
R_{th1}	0.054	0.054	K/W	C_{th1}	0.00005232	0.00005232	Ws/K
R_{th2}	0.103	0.103		C_{th2}	0.0002034	0.0002034	
R_{th3}	0.178	0.178		C_{th3}	0.0002963	0.0002963	
R_{th4}	0.757	0.356		C_{th4}	0.0009103	0.0009103	
R_{th5}	0.682	0.655		C_{th5}	0.002084	0.004434	
R_{th6}	0.202	2.535		C_{th6}	0.024	0.412	



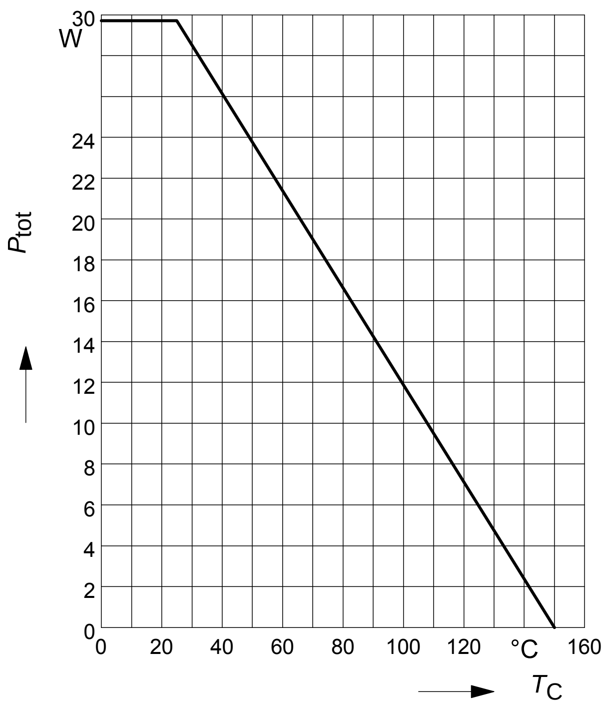
1 Power dissipation

$P_{tot} = f(T_C)$



2 Power dissipation FullPAK

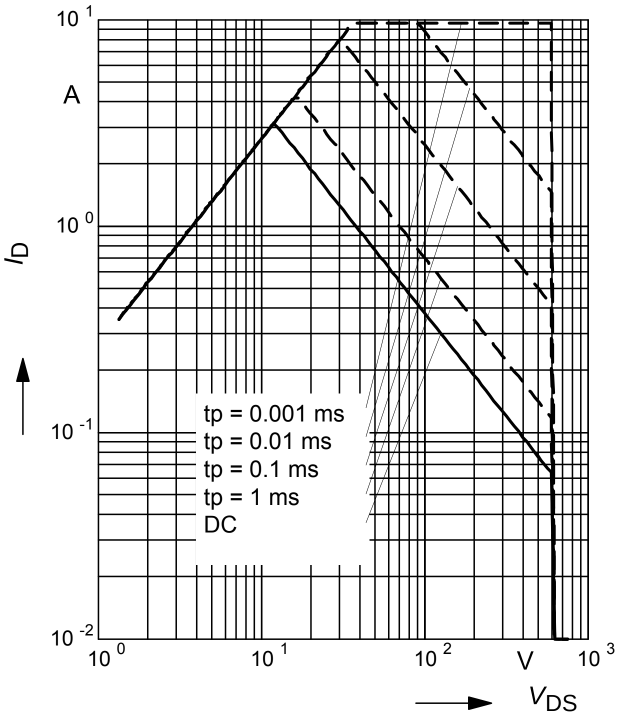
$P_{tot} = f(T_C)$



3 Safe operating area

$I_D = f(V_{DS})$

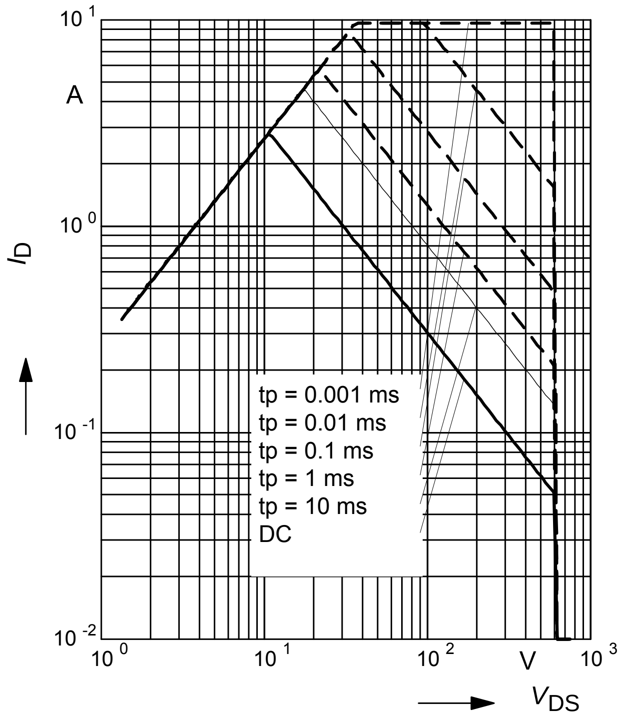
parameter : $D = 0$, T_C=25°C



4 Safe operating area FullPAK

$I_D = f(V_{DS})$

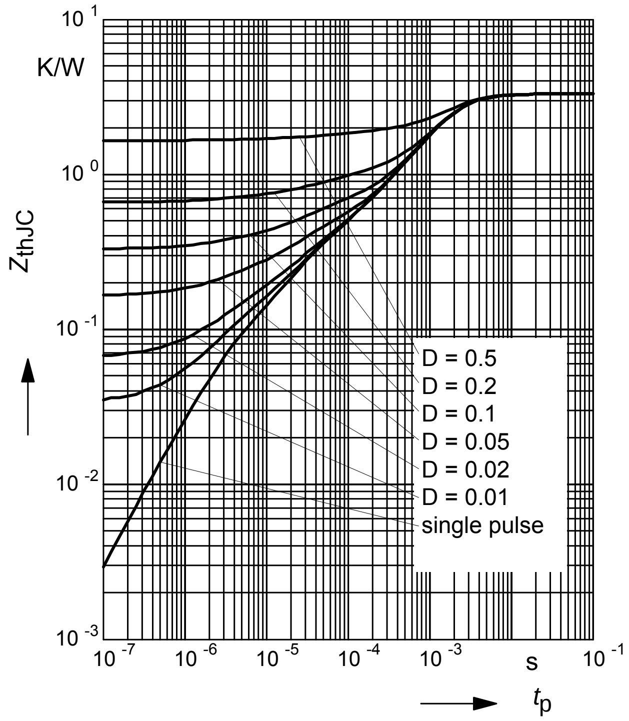
parameter: $D = 0$, T_C = 25°C



5 Transient thermal impedance

$Z_{thJC} = f(t_p)$

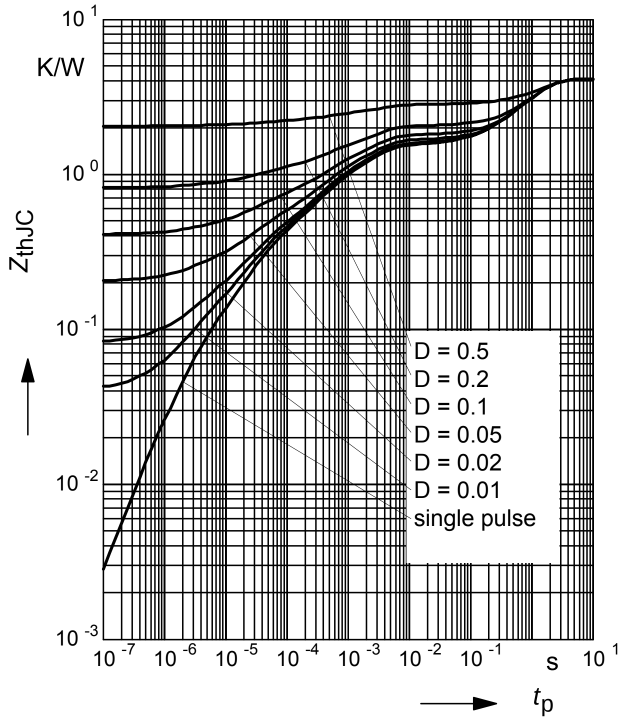
parameter: $D = t_p/T$



6 Transient thermal impedance FullPAK

$Z_{thJC} = f(t_p)$

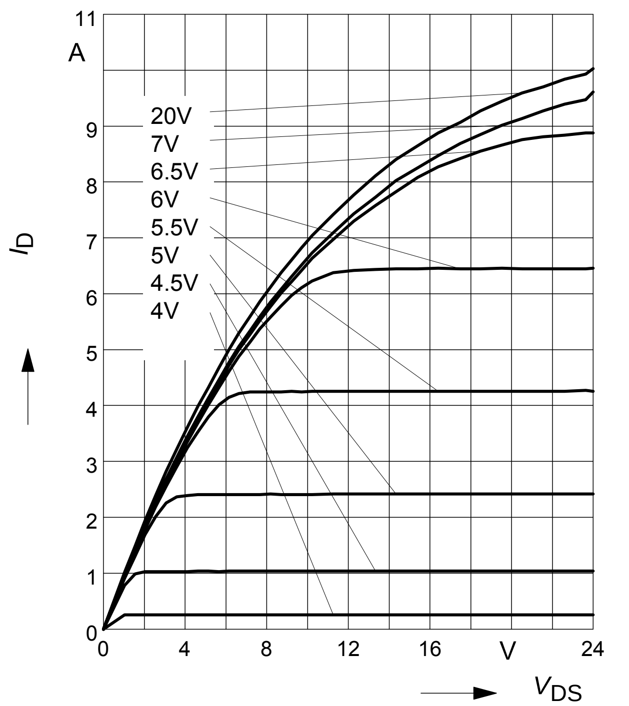
parameter: $D = t_p/t$



7 Typ. output characteristic

$I_D = f(V_{DS})$; T_j=25°C

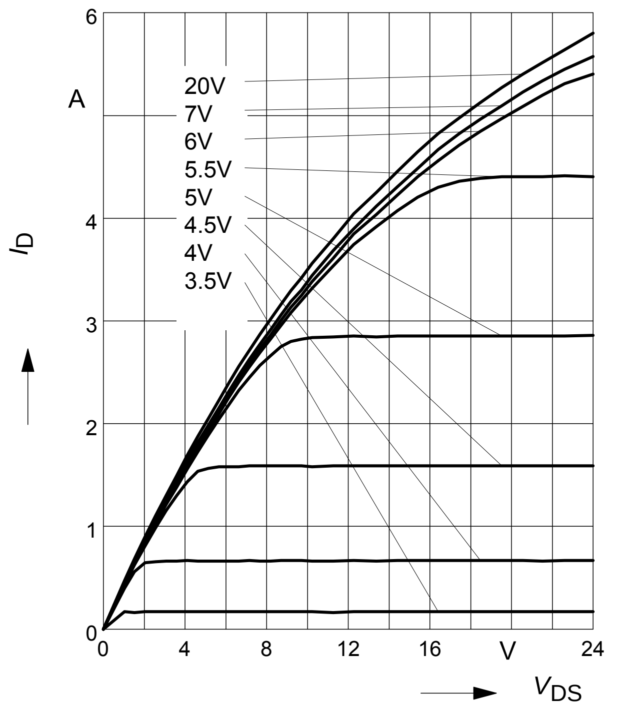
parameter: t_p = 10 µs, V_{GS}



8 Typ. output characteristic

$I_D = f(V_{DS})$; T_j=150°C

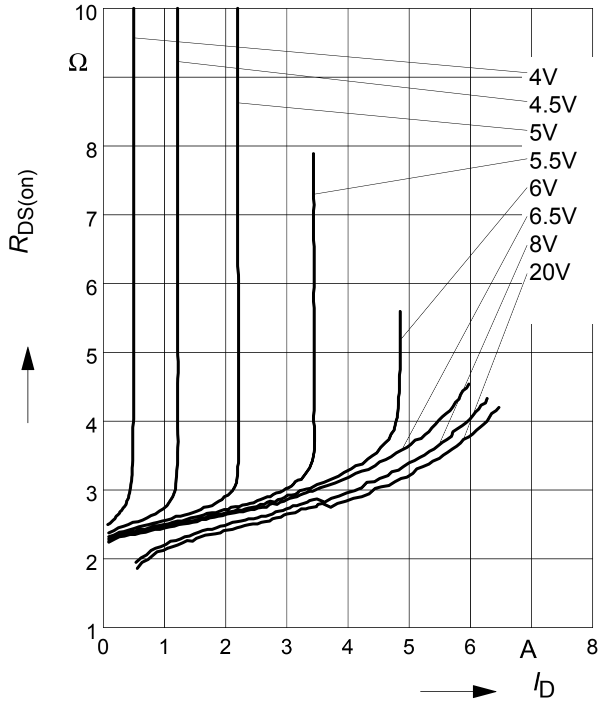
parameter: t_p = 10 µs, V_{GS}



9 Typ. drain-source on resistance

$R_{DS(on)}=f(I_D)$

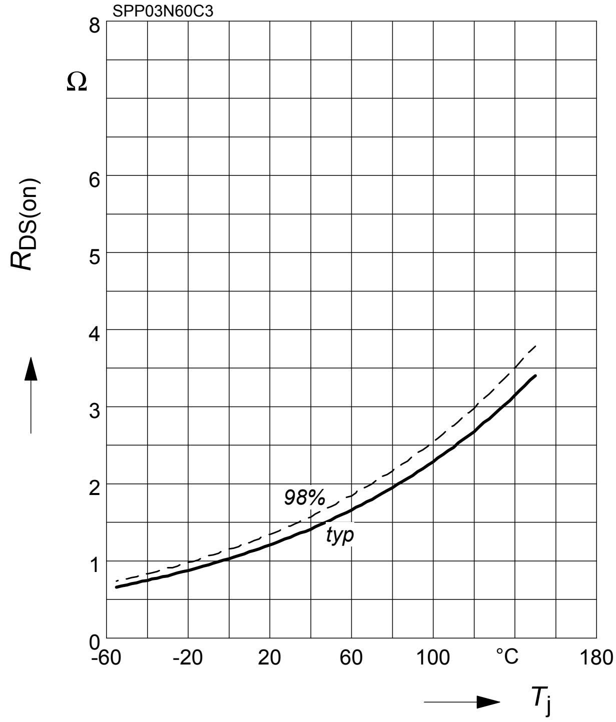
parameter: T_j=150°C, V_{GS}



10 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

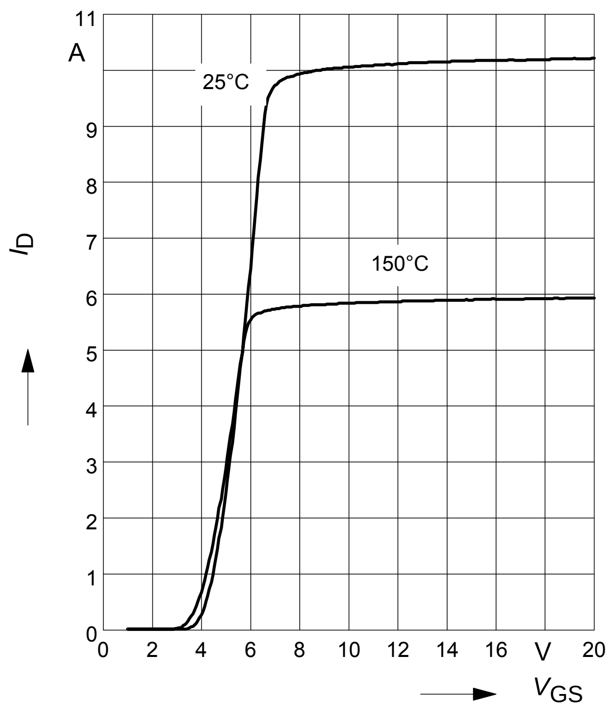
parameter : I_D = 2 A, V_{GS} = 10 V



11 Typ. transfer characteristics

$I_D= f(V_{GS})$; $V_{DS}\geq 2 \times I_D \times R_{DS(on)max}$

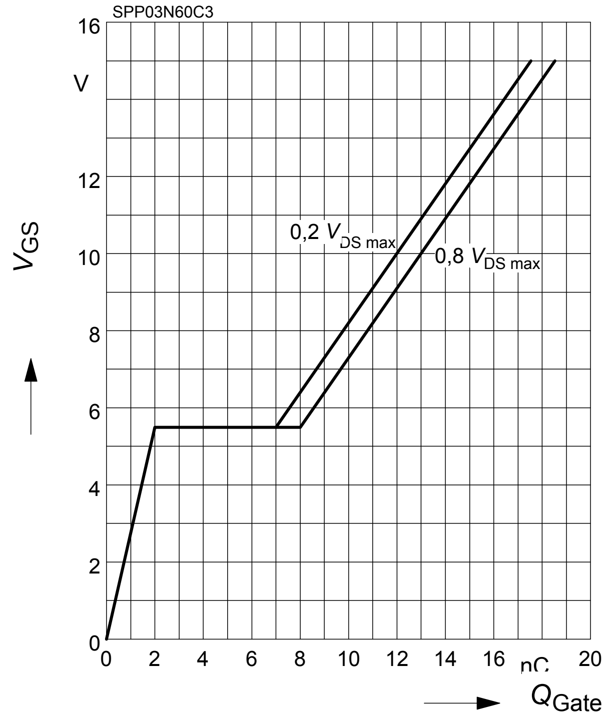
parameter: t_p = 10 µs



12 Typ. gate charge

$V_{GS} = f(Q_{Gate})$

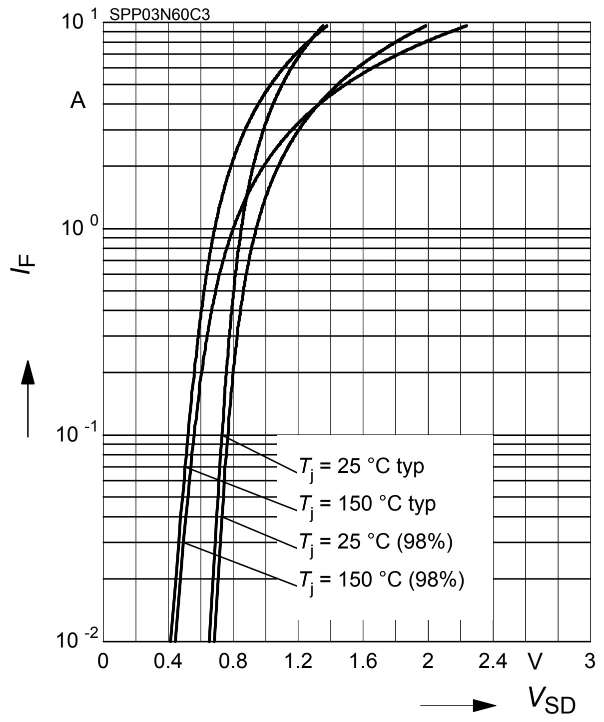
parameter: I_D = 3.2 A pulsed



13 Forward characteristics of body diode

$I_F = f(V_{SD})$

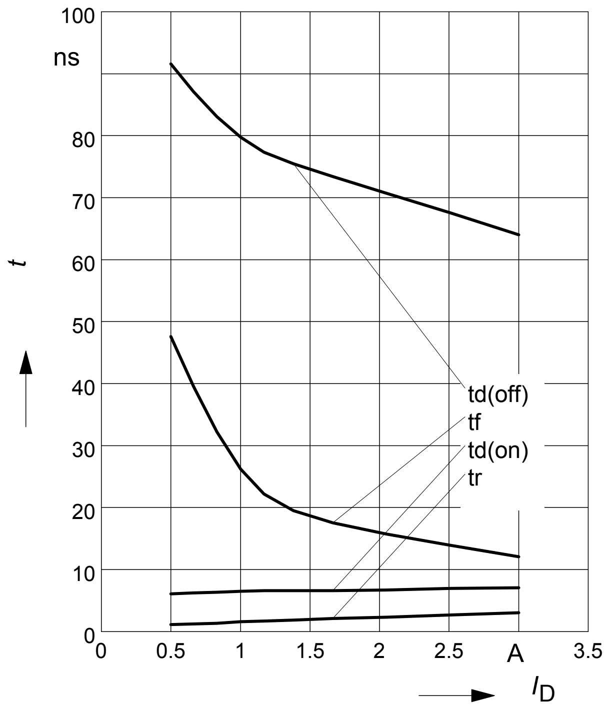
parameter: T_j , t_p = 10 µs



14 Typ. switching time

$t = f(I_D)$, inductive load, T_j=125°C

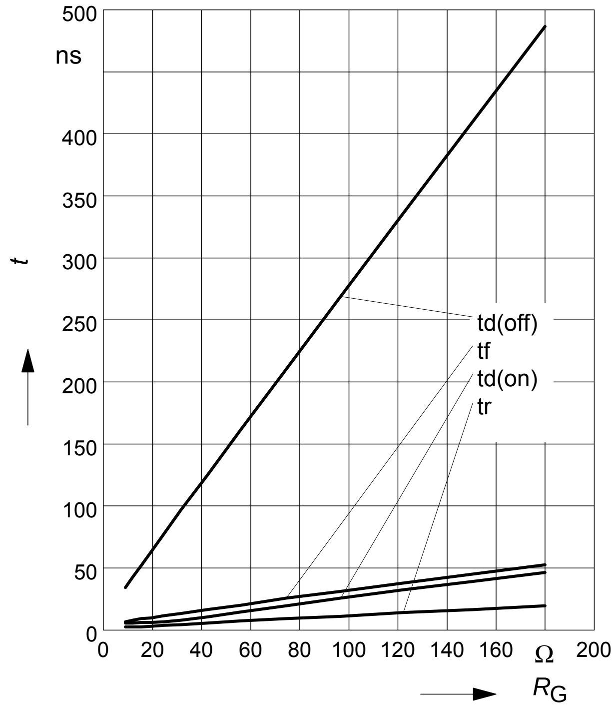
par.: V_{DS}=380V, V_{GS}=0/+13V, R_G=20Ω



15 Typ. switching time

$t = f(R_G)$, inductive load, T_j=125°C

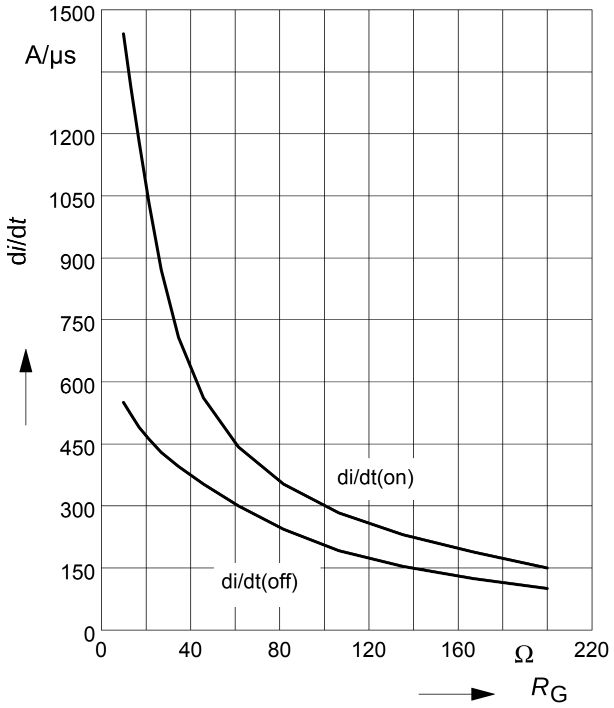
par.: V_{DS}=380V, V_{GS}=0/+13V, I_D=3.2 A



16 Typ. drain current slope

$di/dt = f(R_G)$, inductive load, T_j = 125°C

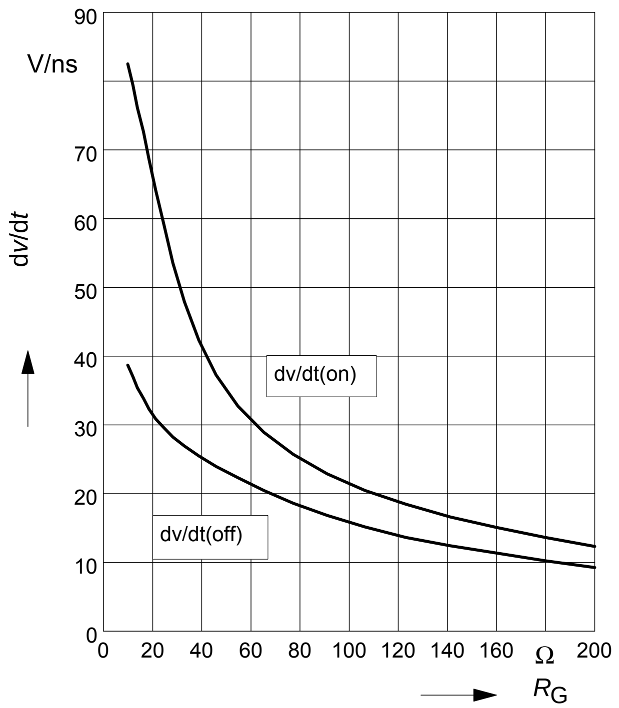
par.: V_{DS}=380V, V_{GS}=0/+13V, I_D=3.2A



17 Typ. drain source voltage slope

$dv/dt = f(R_G)$, inductive load, T_j = 125°C

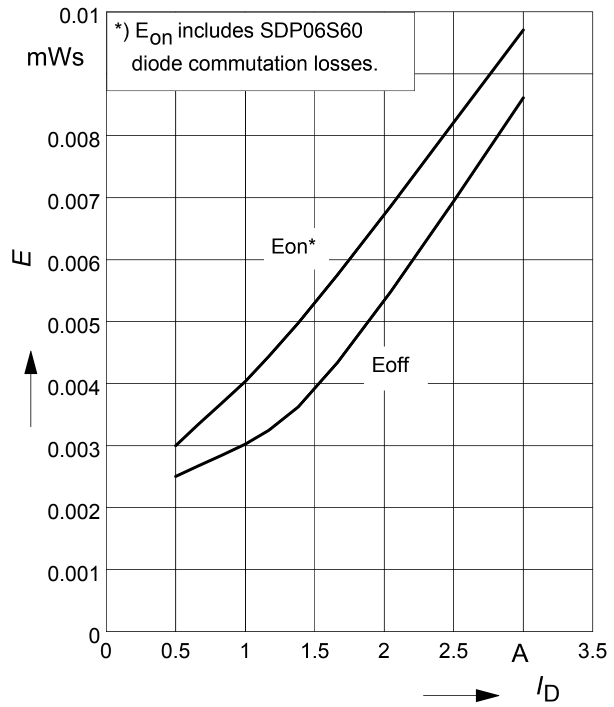
par.: V_{DS}=380V, V_{GS}=0/+13V, I_D=3.2A



18 Typ. switching losses

$E = f(I_D)$, inductive load, T_j=125°C

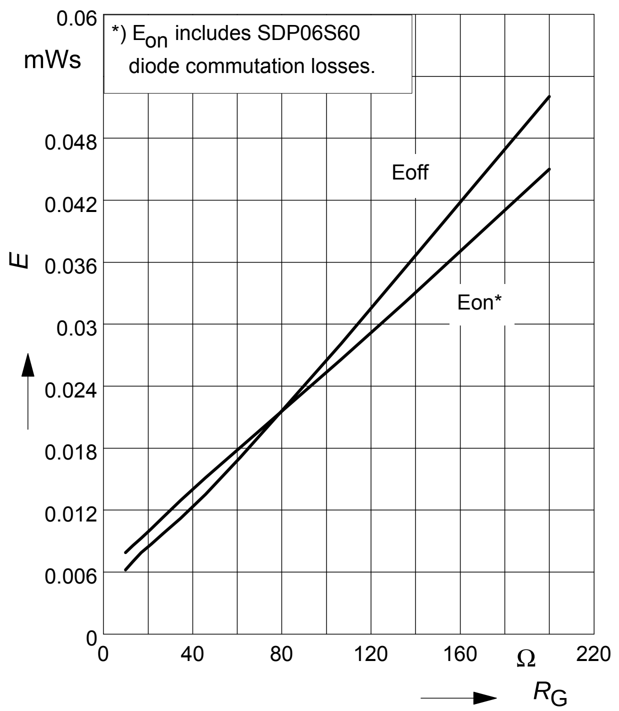
par.: V_{DS}=380V, V_{GS}=0/+13V, R_G=20Ω



19 Typ. switching losses

$E = f(R_G)$, inductive load, T_j=125°C

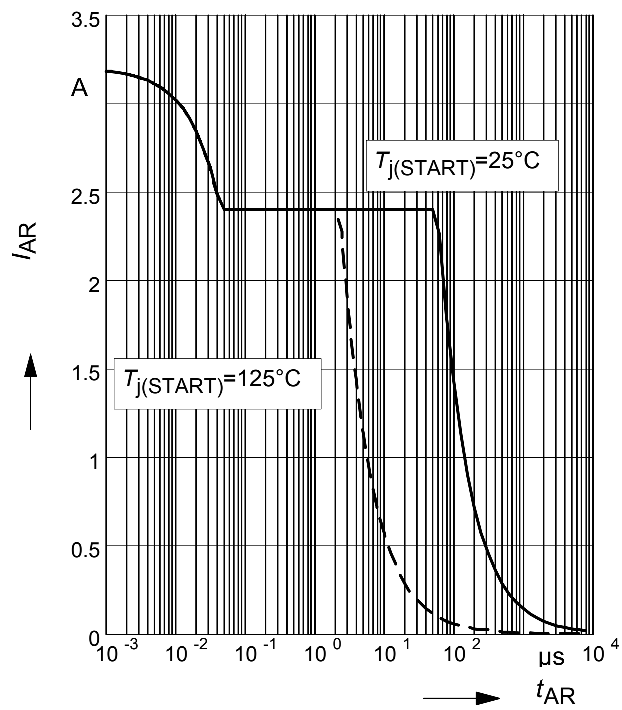
par.: V_{DS}=380V, V_{GS}=0/+13V, I_D=3.2A



20 Avalanche SOA

$I_{AR} = f(t_{AR})$

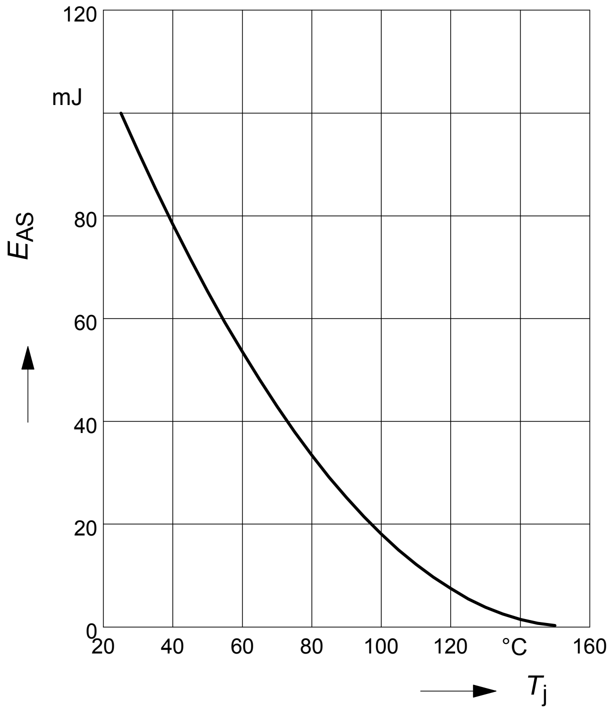
par.: $T_j \leq$ 150 °C



21 Avalanche energy

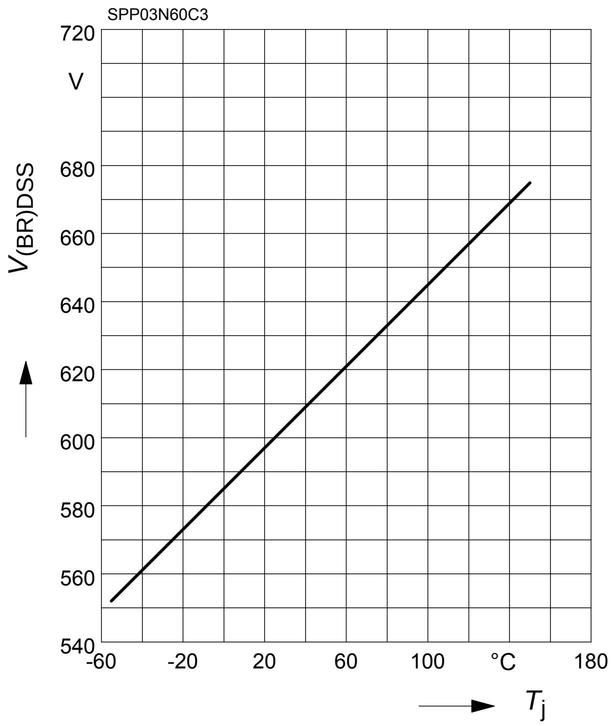
$E_{AS} = f(T_j)$

par.: I_D = 2.4 A, V_{DD} = 50 V



22 Drain-source breakdown voltage

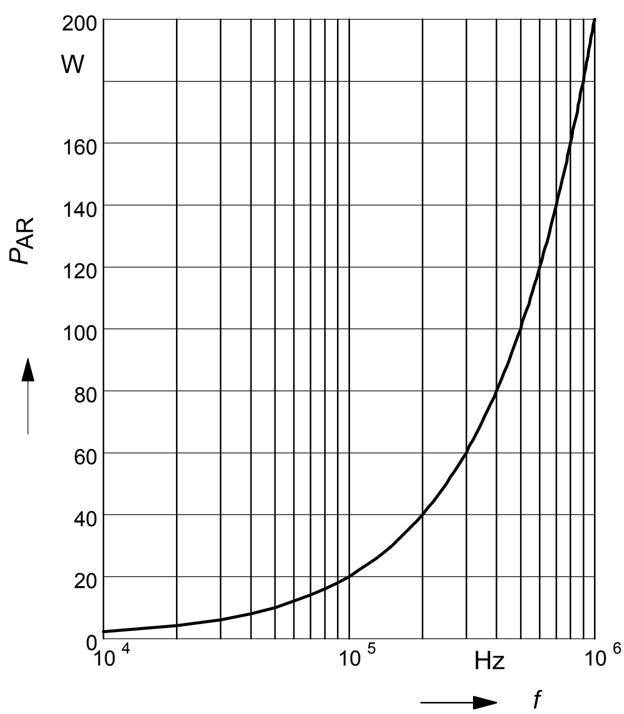
$V_{(BR)DSS} = f(T_j)$



23 Avalanche power losses

$P_{AR} = f(f)$

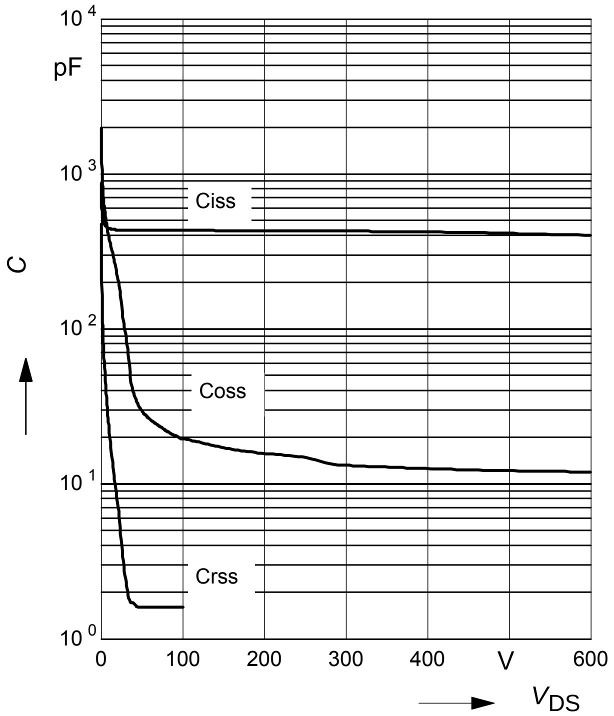
parameter: E_{AR}=0.2mJ



24 Typ. capacitances

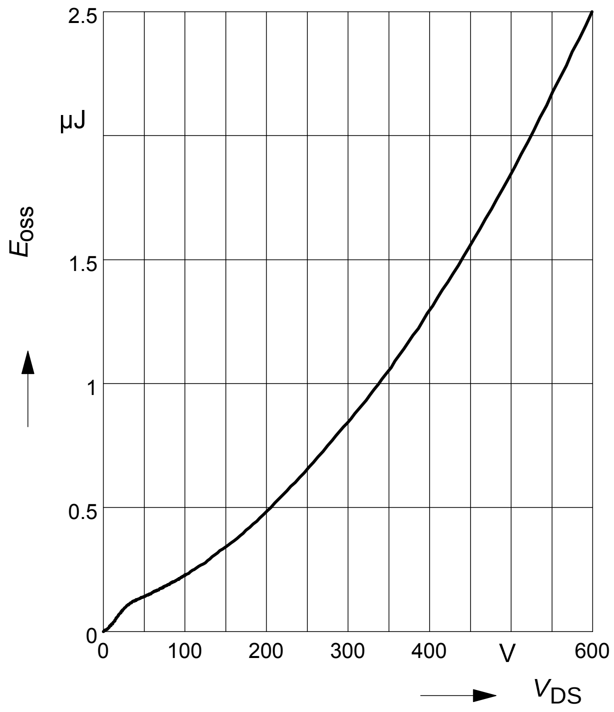
$C = f(V_{DS})$

parameter: V_{GS}=0V, f=1 MHz

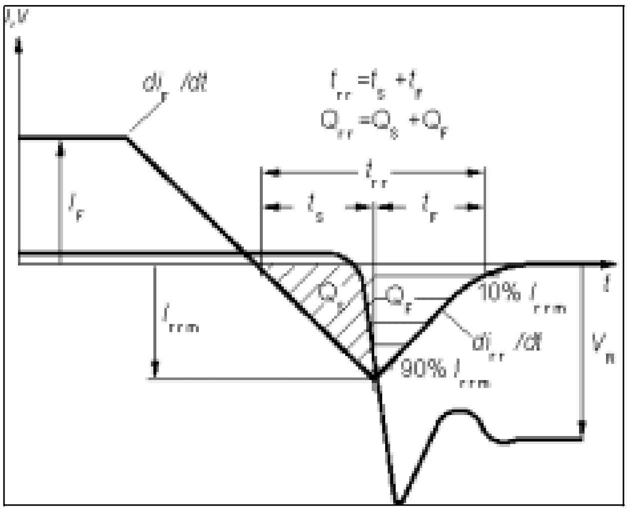


25 Typ. C_{oss} **stored energy**

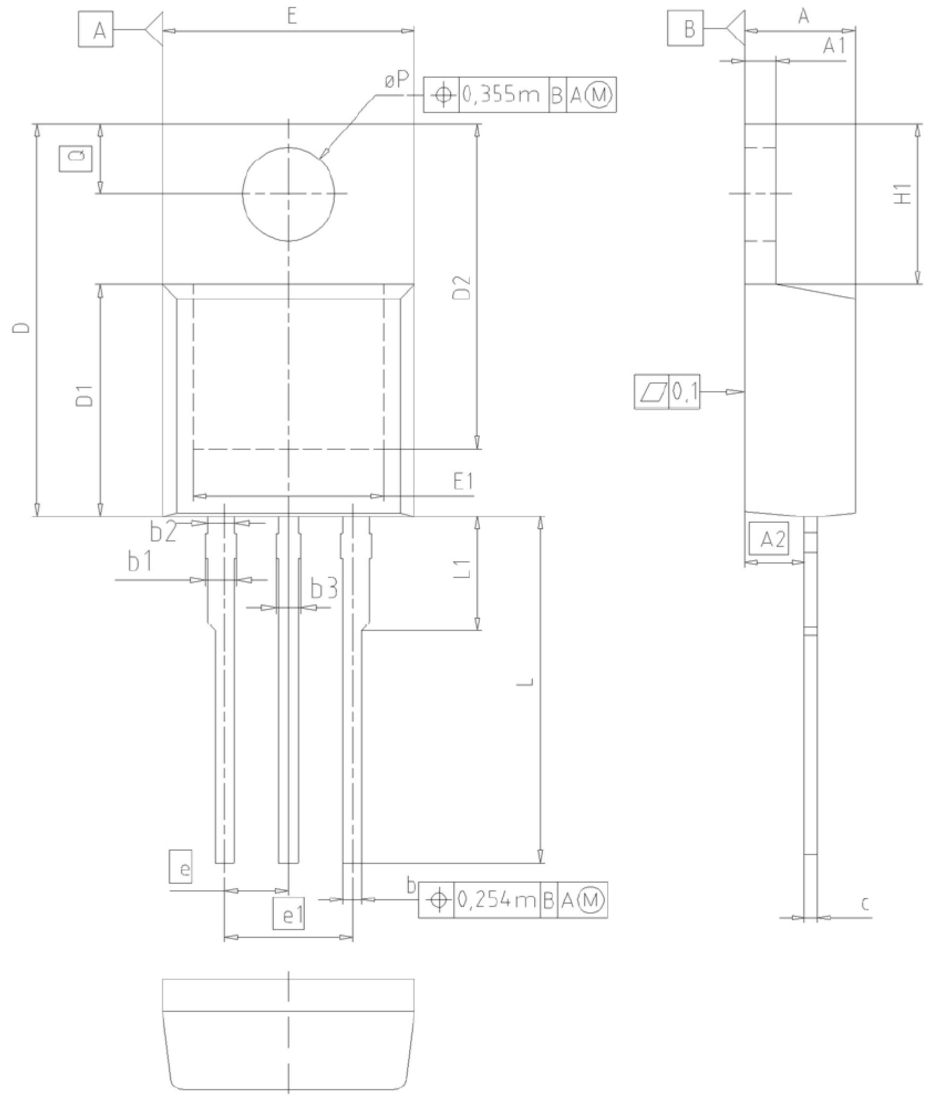
$E_{oss}=f(V_{DS})$



Definition of diodes switching characteristics



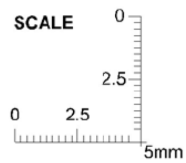
PG-TO220-3-1, PG-TO220-3-21 : Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

DOCUMENT NO.
Z8B00003318

SCALE



EUROPEAN PROJECTION

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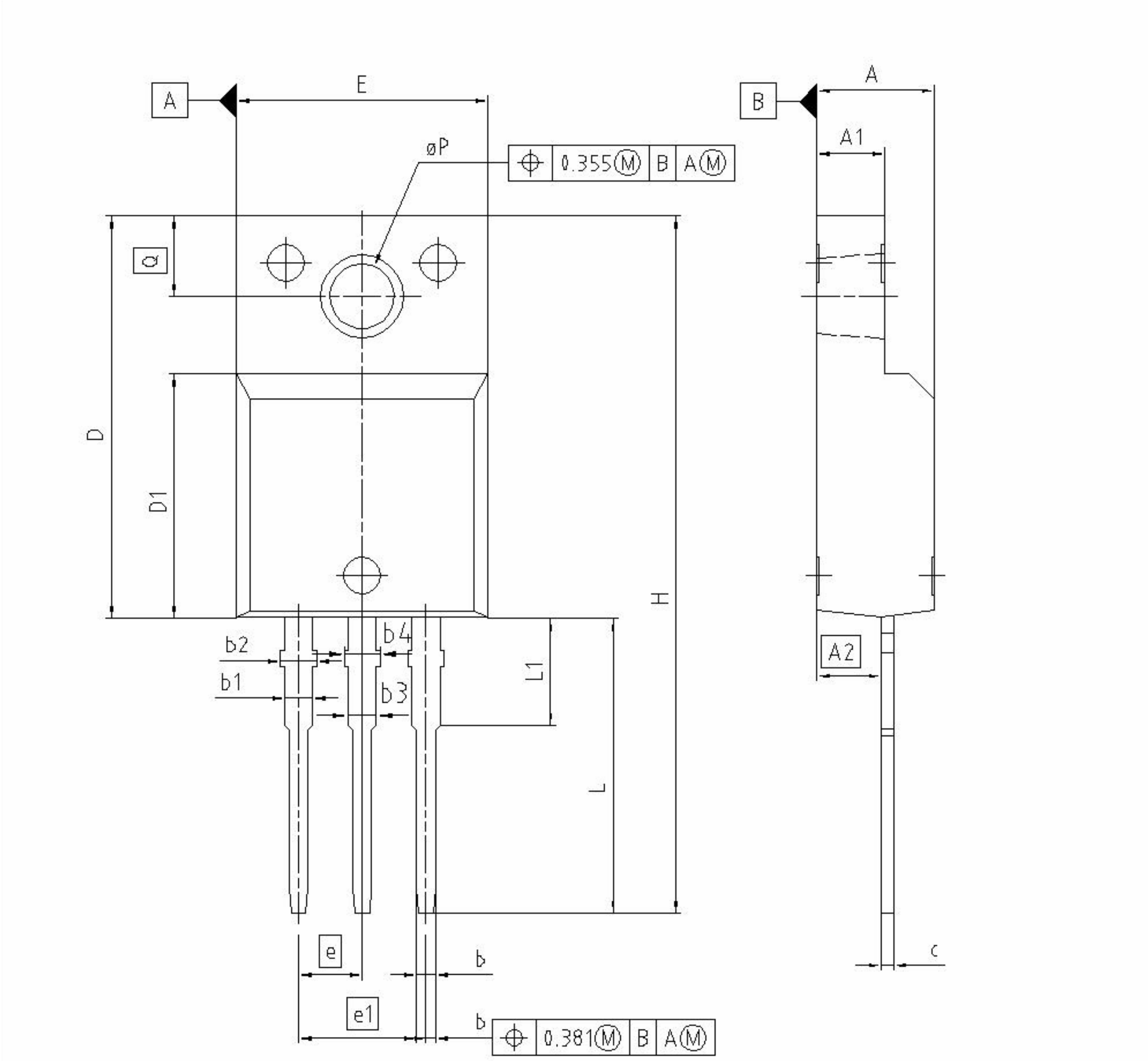
23-08-2007

REVISION
05

PG-TO220-3-31/3-111 Fully isolated package (2500VAC; 1 minute)



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.55	4.85	0.179	0.191
A1	2.55	2.85	0.100	0.112
A2	2.42	2.72	0.095	0.107
b	0.65	0.85	0.026	0.033
b1	0.95	1.33	0.037	0.052
b2	0.95	1.51	0.037	0.059
b3	0.65	1.33	0.026	0.052
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.85	16.15	0.624	0.636
D1	9.53	9.83	0.375	0.387
E	10.35	10.65	0.407	0.419
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H	29.45	29.75	1.159	1.171
L	13.45	13.75	0.530	0.541
L1	3.15	3.45	0.124	0.136
øP	2.95	3.20	0.116	0.126
Q	3.15	3.50	0.124	0.138

REFERENCE
../..
SCALE 0 2.5 5mm
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FILE TO220_2

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